



## DOCUMENT CHANGE REQUEST

DCR number	792	Changes required for:	General	Originator:	Geraldine Chaumont
Date:	2013/07/17	Date sent:	2013/04/25	Organisation:	STMicroelectronics
Status:	IMPLEMENTED				

Title: TRANSISTORS, POWER, MOSFET, P-CHANNEL, RAD-HARD BASED ON TYPE STRH40P10

Number: 5205/025 Issue: 2

Other documents affected:

Page:

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Paragraph:

2.11.1

Original wording:

With VGS bias = -20V and VDS = -100V during irradiation

Proposed wording:

With VGS bias = -15V and VDS = 0V during irradiation

Justification:

The actual bias condition during irradiation is not aligned nor with the customer applications nor with the bias condition held for STRH100N10 (5205/021).

Attachments:

N/A

Modifications:

N/A

Approval signature:

Date signed:

2013-07-17